

# PEMD3; PIMD3; PUMD3

NPN/PNP resistor-equipped transistors;

R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

Rev. 10 — 15 November 2009

Product data sheet

## 1. Product profile

### 1.1 General description

NPN/PNP Resistor-Equipped Transistors (RET).

Table 1. Product overview

Type number	Package		PNP/PNP complement	NPN/PNP complement
	NXP	JEITA		
PEMD3	SOT666	-	PEMB11	PEMH11
PIMD3	SOT457	SC-74	-	-
PUMD3	SOT363	SC-88	PUMB11	PUMH11

### 1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

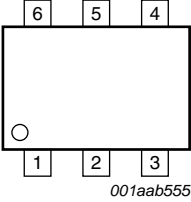
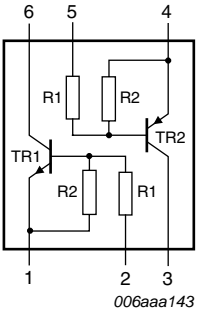
### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	50	V
I <sub>O</sub>	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		7	10	13	k $\Omega$
R2/R1	bias resistor ratio		0.8	1	1.2	

## 2. Pinning information

**Table 3. Pinning**

Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1		

## 3. Ordering information

**Table 4. Ordering information**

Type number	Package		Version
	Name	Description	
PEMD3	-	plastic surface mounted package; 6 leads	SOT666
PIMD3	SC-74	plastic surface mounted package; 6 leads	SOT457
PUMD3	SC-88	plastic surface mounted package; 6 leads	SOT363

## 4. Marking

**Table 5. Marking codes**

Type number	Marking code <sup>[1]</sup>
PEMD3	D3
PIMD3	M7
PUMD3	D*3

[1] \* = -: made in Hong Kong  
 \* = p: made in Hong Kong  
 \* = t: made in Malaysia  
 \* = W: made in China

## 5. Limiting values

**Table 6. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
<b>Per transistor; for the PNP transistor with negative polarity</b>						
V <sub>CB0</sub>	collector-base voltage	open emitter	-	50	V	
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V	
V <sub>EBO</sub>	emitter-base voltage	open collector	-	10	V	
V <sub>I</sub>	input voltage TR1					
	positive		-	+40	V	
	negative		-	-10	V	
	input voltage TR2					
	positive		-	+10	V	
	negative		-	-40	V	
I <sub>O</sub>	output current (DC)		-	100	mA	
I <sub>CM</sub>	peak collector current		-	100	mA	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C				
	SOT363		[1]	-	200	mW
	SOT457		[2]	-	300	mW
	SOT666		[1][3]	-	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C	
T <sub>j</sub>	junction temperature		-	150	°C	
T <sub>amb</sub>	ambient temperature		-65	+150	°C	
<b>Per device</b>						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C				
	SOT363		[1]	-	300	mW
	SOT457		[2]	-	600	mW
	SOT666		[1][3]	-	300	mW

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB with 65  $\mu$ m copper strip line, standard footprint.

[3] Reflow soldering is the only recommended soldering method.

## 6. Thermal characteristics

**Table 7. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT363		[1]	-	625	K/W
	SOT457		[2]	-	417	K/W
	SOT666		[1][3]	-	625	K/W
<b>Per device</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT363		[1]	-	416	K/W
	SOT457		[2]	-	208	K/W
	SOT666		[1][3]	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB with 65 μm copper strip line, standard footprint.

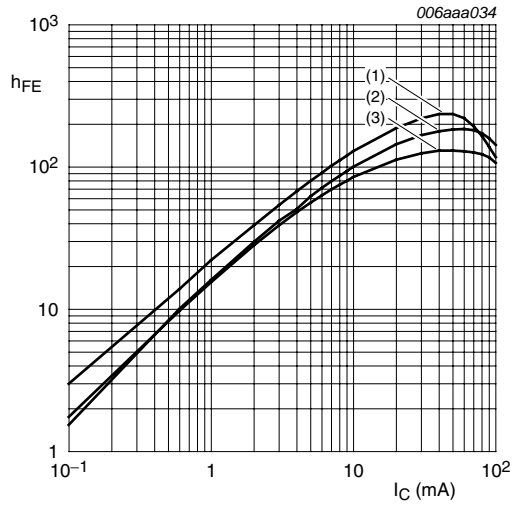
[3] Reflow soldering is the only recommended soldering method.

## 7. Characteristics

**Table 8. Characteristics**

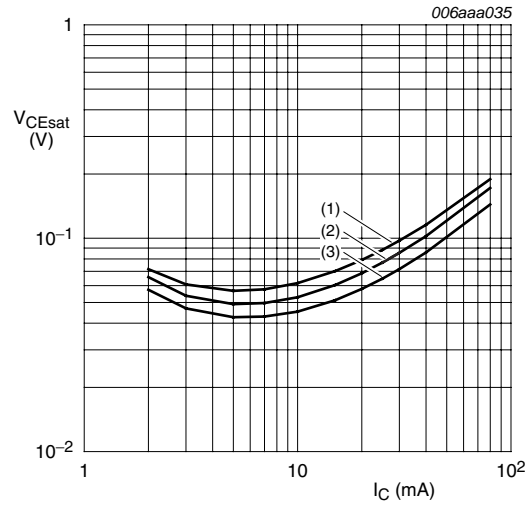
$T_{amb} = 25\text{ °C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor; for the PNP transistor with negative polarity</b>						
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 50\text{ V}; I_E = 0\text{ A}$	-	-	100	nA
$I_{CEO}$	collector-emitter cut-off current	$V_{CE} = 30\text{ V}; I_B = 0\text{ A}$	-	-	1	μA
		$V_{CE} = 30\text{ V}; I_B = 0\text{ A}; T_j = 150\text{ °C}$	-	-	50	μA
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	400	μA
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}; I_C = 5\text{ mA}$	30	-	-	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5\text{ V}; I_C = 100\text{ μA}$	-	1.1	0.8	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3\text{ V}; I_C = 10\text{ mA}$	2.5	1.8	-	V
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	
$C_c$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_C = 0\text{ A}; f = 1\text{ MHz}$	-	-	-	
		TR1 (NPN)	-	-	2.5	pF
		TR2 (PNP)	-	-	3	pF



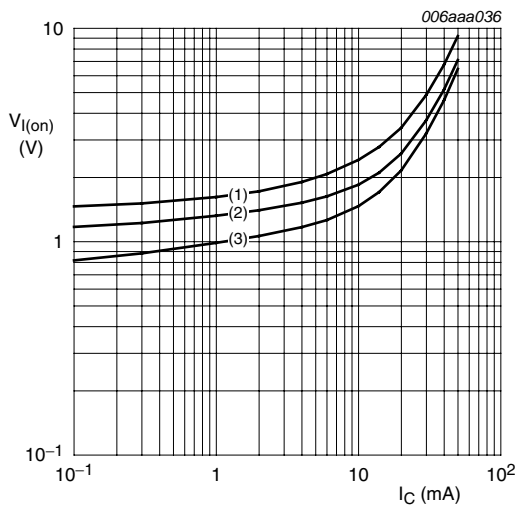
$V_{CE} = 5 \text{ V}$   
 (1)  $T_{amb} = 150 \text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -40 \text{ }^\circ\text{C}$

**Fig 1. TR1 (NPN): DC current gain as a function of collector current; typical values**



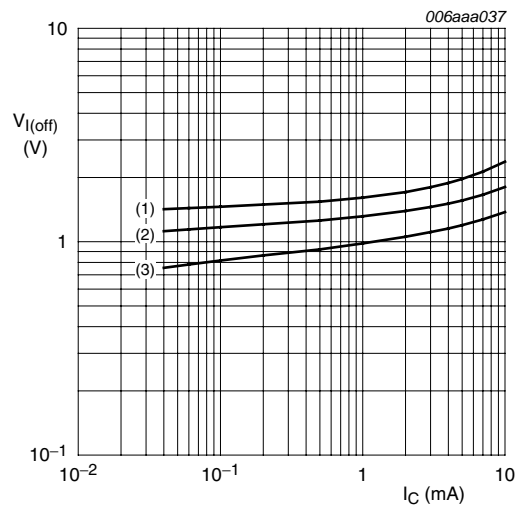
$I_C/I_B = 20$   
 (1)  $T_{amb} = 100 \text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -40 \text{ }^\circ\text{C}$

**Fig 2. TR1 (NPN): Collector-emitter voltage as a function of collector current; typical values**



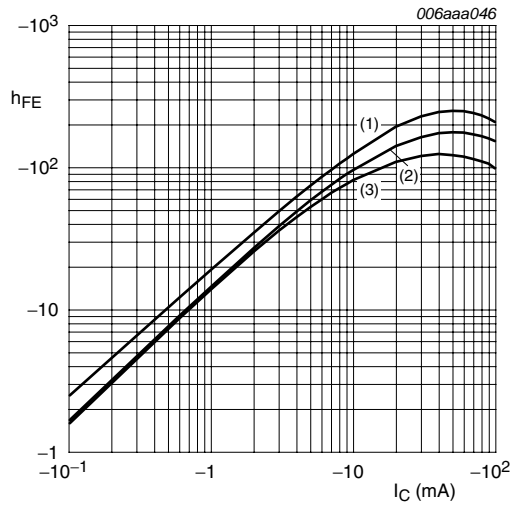
$V_{CE} = 0.3 \text{ V}$   
 (1)  $T_{amb} = -40 \text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100 \text{ }^\circ\text{C}$

**Fig 3. TR1 (NPN): On-state input voltage as a function of collector current; typical values**



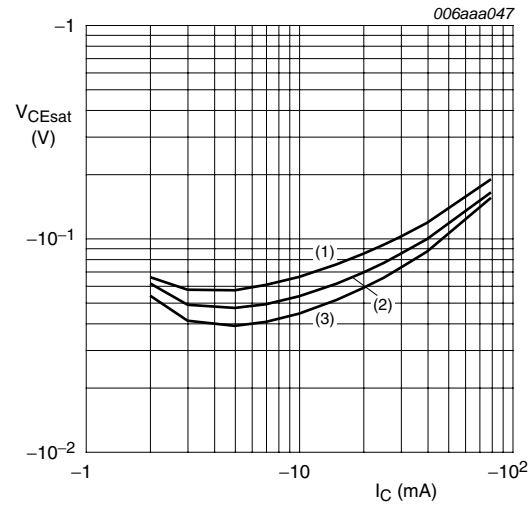
$V_{CE} = 5 \text{ V}$   
 (1)  $T_{amb} = -40 \text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100 \text{ }^\circ\text{C}$

**Fig 4. TR1 (NPN): Off-state input voltage as a function of collector current; typical values**



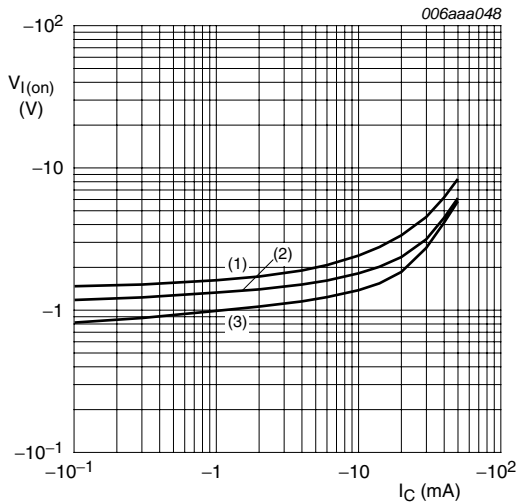
$V_{CE} = -5 \text{ V}$   
 (1)  $T_{amb} = 150 \text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -40 \text{ }^\circ\text{C}$

**Fig 5. TR2 (PNP): DC current gain as a function of collector current; typical values**



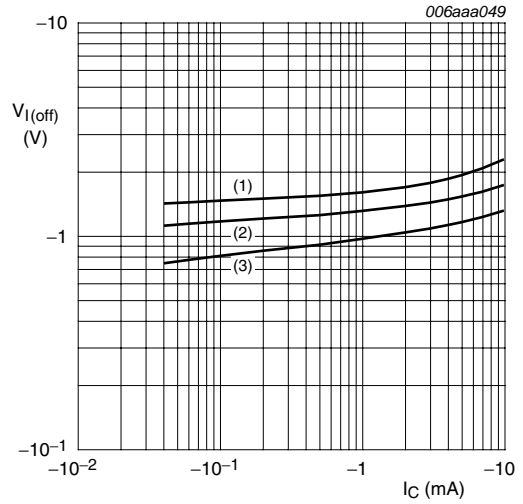
$I_C/I_B = 20$   
 (1)  $T_{amb} = 100 \text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -40 \text{ }^\circ\text{C}$

**Fig 6. TR2 (PNP): Collector-emitter voltage as a function of collector current; typical values**



$V_{CE} = -0.3 \text{ V}$   
 (1)  $T_{amb} = -40 \text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100 \text{ }^\circ\text{C}$

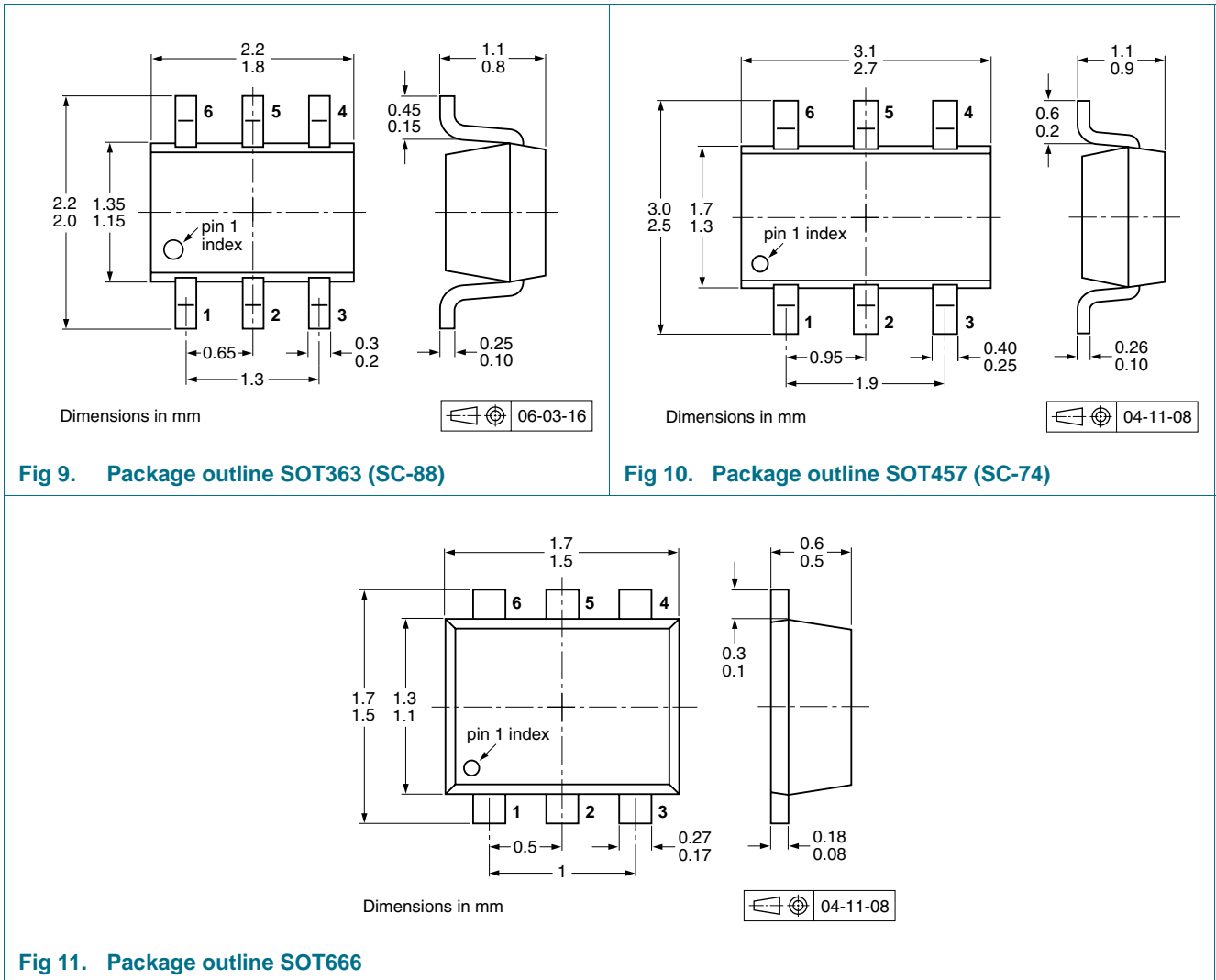
**Fig 7. TR2 (PNP): On-state input voltage as a function of collector current; typical values**



$V_{CE} = -5 \text{ V}$   
 (1)  $T_{amb} = -40 \text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100 \text{ }^\circ\text{C}$

**Fig 8. TR2 (PNP): Off-state input voltage as a function of collector current; typical values**

## 8. Package outline



## 9. Packing information

**Table 9. Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

Type number	Package	Description	Packing quantity			
			3000	4000	8000	10000
PEMD3	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-
PIMD3	SOT457	4 mm pitch, 8 mm tape and reel; T1 <a href="#">[2]</a>	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2 <a href="#">[3]</a>	-125	-	-	-165
PUMD3	SOT363	4 mm pitch, 8 mm tape and reel; T1 <a href="#">[2]</a>	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2 <a href="#">[3]</a>	-125	-	-	-165

[1] For further information and the availability of packing methods, see [Section 12](#).

[2] T1: normal taping

[3] T2: reverse taping



## 10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMD3_PIMD3_PUMD3_10	20091115	Product data sheet	-	PEMD3_PIMD3_PUMD3_9
Modifications:	<ul style="list-style-type: none"> <li>This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.</li> <li><a href="#">Figure 9 "Package outline SOT363 (SC-88)"</a>: updated</li> </ul>			
PEMD3_PIMD3_PUMD3_9	20050518	Product data sheet	-	PEMD3_PIMD3_PUMD3_8
PEMD3_PIMD3_PUMD3_8	20041206	Product data sheet	-	PEMD3_PUMD3_7

## 11. Legal information

### 11.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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